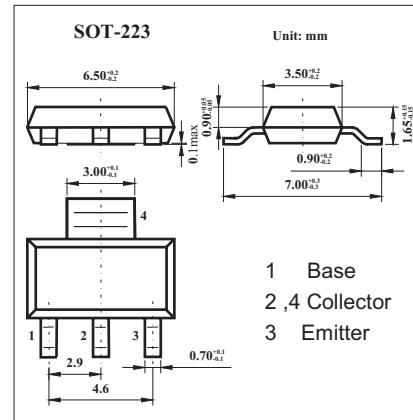
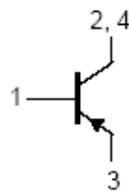


PNP medium power transistor

KCP69

■ Features

- High current (max. 1 A)
- Low voltage (max. 20 V).



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-32	V
Collector-emitter voltage	V _{CEO}	-20	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current (DC)	I _C	-1	A
Peak collector current	I _{CM}	-2	A
Peak base current	I _{BM}	-200	mA
Total power dissipation T _{amb} ≤ 25 °C	P _D	1.35	W
Storage temperature	T _{stg}	-65 to +150	°C
Junction temperature	T _j	150	°C
Operating ambient temperature	T _{amb}	-65 to +150	°C
Thermal resistance from junction to ambient	R _{th(j-a)}	91	K/W
Thermal resistance from junction to solder point	R _{th(j-s)}	10	K/W

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I _{CB0}	I _E = 0 A; V _{CB} = -25 V			-100	nA
		I _E = 0 A; V _{CB} = -25 V; T _j = 150 °C			-10	μ A
Emitter cutoff current	I _{EB0}	I _C = 0 A; V _{EB} = -5 V			-100	nA
DC current gain	h _{FE}	V _{CE} = -10 V; I _C = -5 mA	50			
		V _{CE} = -1 V; I _C = -500 mA	85		375	
		V _{CE} = -1 V; I _C = -1 A	60			
		V _{CE} = -1 V; I _C = -500 mA	100		250	
DC current gain BCP69-16 BCP69-25			160		375	
Collector-emitter saturation voltage	V _{CEsat}	I _C = -1 A; I _B = -100 mA;			-500	mV
Base-emitter voltage	V _{BE}	V _{CE} = -10 V; I _C = -5 mA		-620		mV
		V _{CE} = -1 V; I _C = -1 A			-1	V
Collector capacitance	C _c	I _E = ie = 0 A; V _{CB} = -5 V; f = 1 MHz		48		pF
Transition frequency	f _T	I _C = -10 mA; V _{CE} = -5 V; f = 100 MHz	40			MHz

■ Marking

Marking	BCP69
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KCP69

■ Typical Characteristics

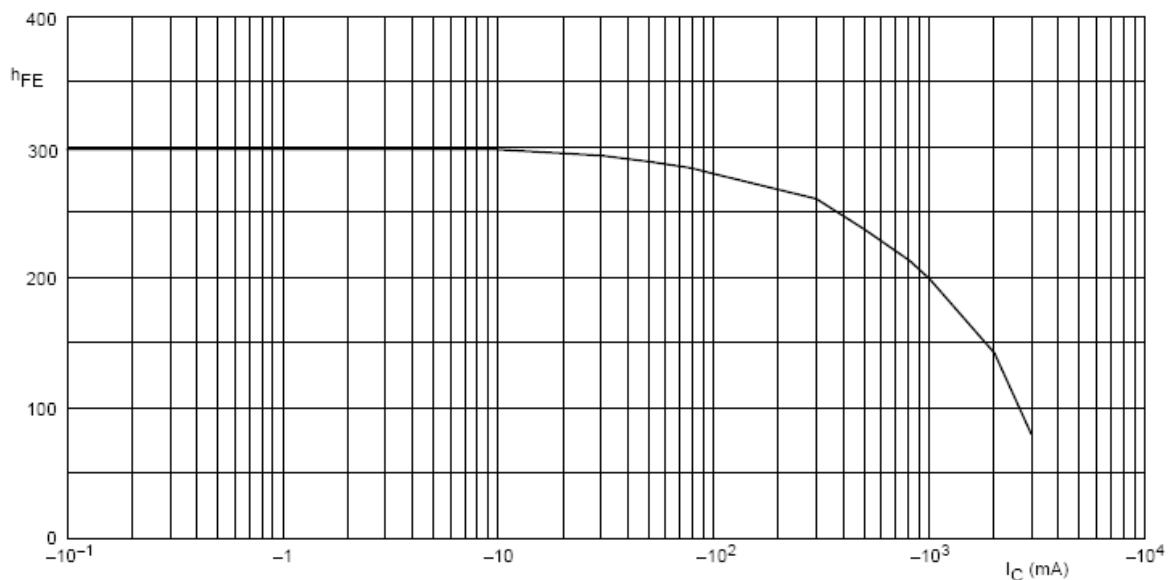
 $V_{CE} = -1$ V.

Fig.1 DC current gain; typical values.